NSN 5961-01-021-5631

No Fiig: A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-021-5631 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Overall Height:** 0.185 inches **Overall Width:** 0.271 inches **End Application:** Ea-6b prowler, a-6e intruder aircraft. B-1 aircraft support equipment. **Component Name And Quantity:** 5 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon 9th transistor Voltage Rating In Volts Per Characteristic: 20.0 collector to base voltage/static/emitter open all transistor and 15.0 collector to emitter voltage/static/base open all transistor and 5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 750.0 milliwatts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:**